

HIGH POWER TERMINATION

100W

When properly mounted on an appropriate heat sink, this chip device provides high power dissipation capabilities. Ideal for ferrite isolator applications, the improved thin film design technology and laser trimming provide proven RF power capabilities to meet the demands of today's CMA and WCDMA system requirements.

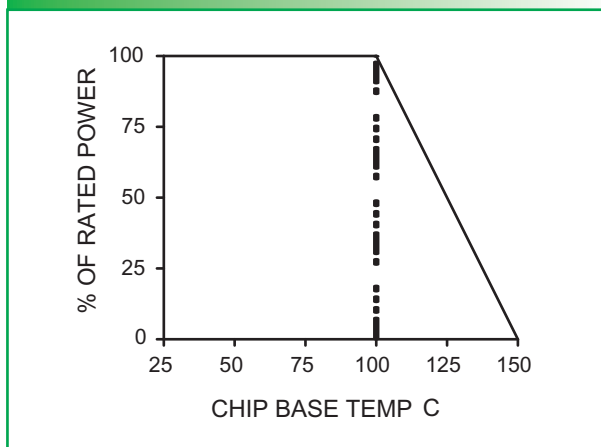
- Environmentally friendly ALN substrate
- Hi-performance thin film element
- Power Handling of 100Watts
- New adhesion process results in improved terminal strength
- On-chip matching network improves frequency performance over the DC-3 GHz frequency range
- **Rohs compliant**

SPECIFICATIONS

Parameters	Specifications
Frequency Range	DC to 3 GHz
Power	100 Watts*
VSWR	1.15:1 max
Resistance	50 ohms +/- 2 %
Operating Temperature	-55 C to 150 C
Substrate	Aluminum Nitride

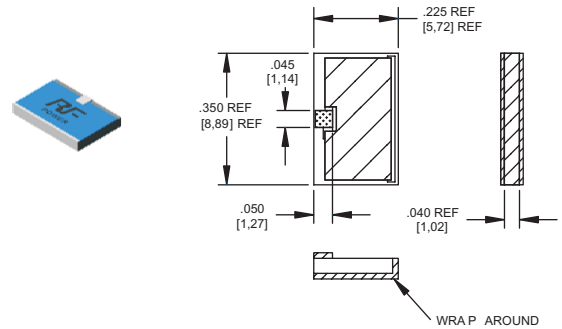
* Refer to average power derating curve chart.

AVERAGE POWER DERATING CURVE



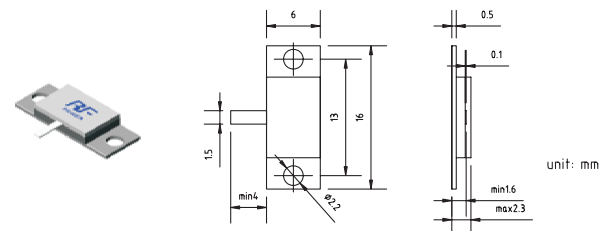
CHIP DIMENSIONS

MANC350225T050G

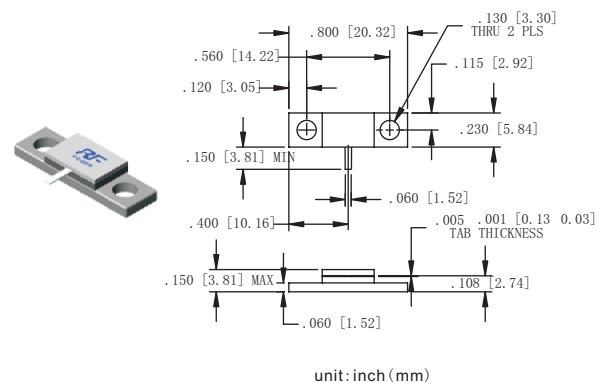


FLANGED DIMENSIONS

MANF350225T050G-1



MANF350225T050G-2



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